

Silicon NPN Power Transistors

2SC3559

DESCRIPTION

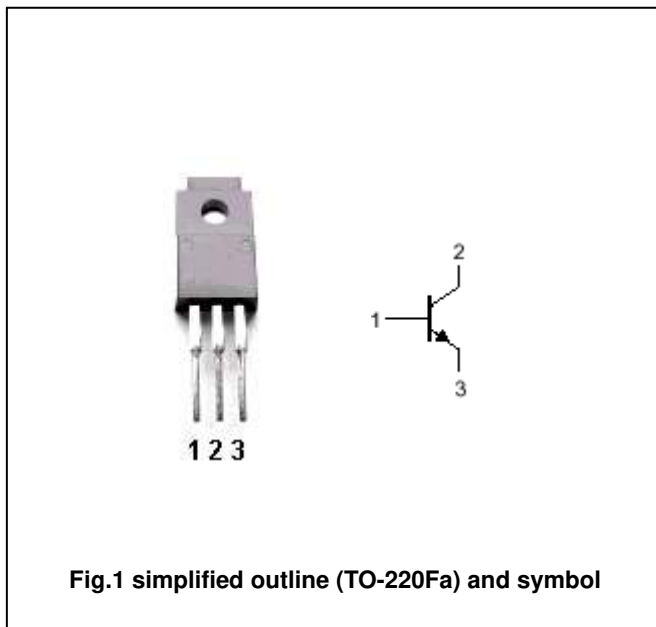
- With TO-220Fa package
- High breakdown voltage
- High speed switching

APPLICATIONS

- Switching regulator and high voltage switching applications
- High speed DC-DC converter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		3	A
I_{CM}	Collector current-Peak		5	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	30	W
		$T_a=25^\circ\text{C}$	2	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon NPN Power Transistors

2SC3559

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	800			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA, I _E =0	900			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.8A; I _B =0.16A			0.6	V
V _{BEsat}	Base-emitter saturation voltage	I _C =0.8A; I _B =0.16A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =0.8A; V _{CE} =5V	10			

Switching times

t _r	Rise time	I _{B1} =0.08A; I _{B2} =-0.2A V _{CC} ≈400V; R _L =500Ω			1.0	μs
t _s	Storage time				4.0	μs
t _f	Fall time				1.0	μs

PACKAGE OUTLINE

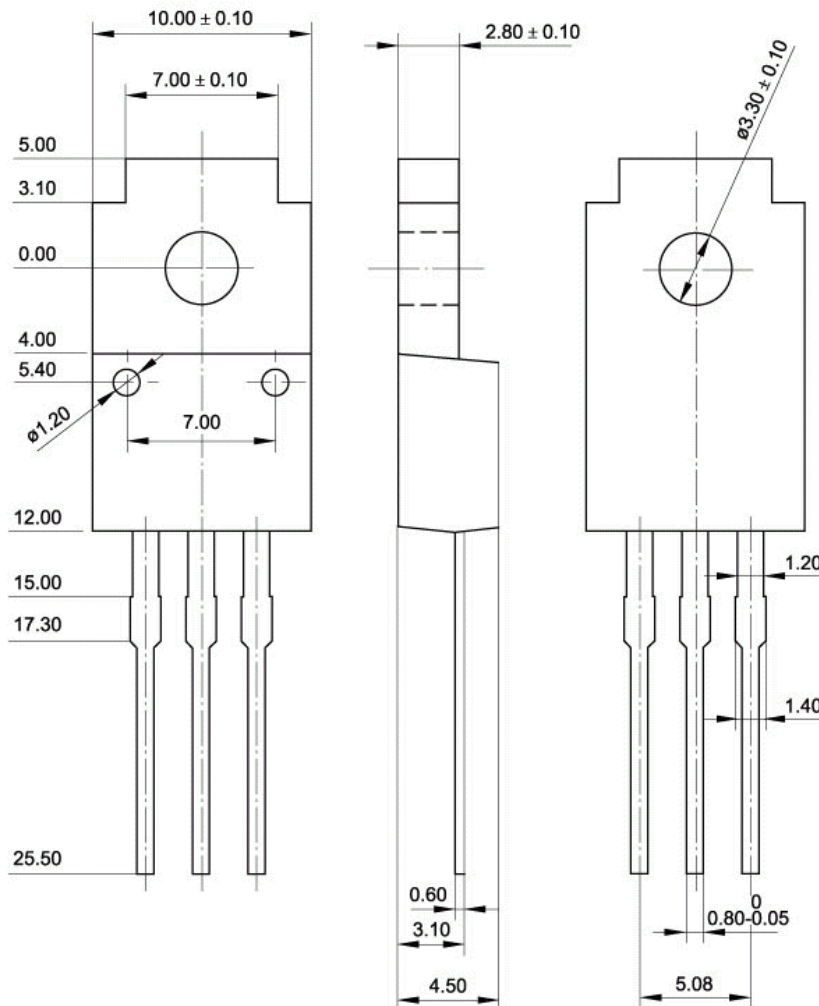


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

Silicon NPN Power Transistors

2SC3559

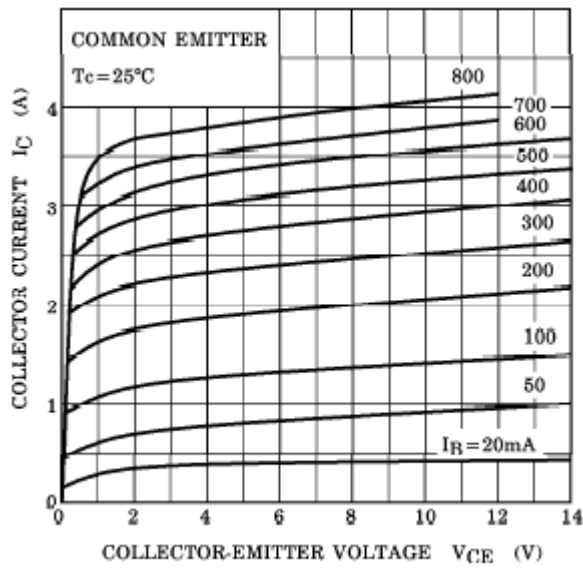


Fig.3 Static Characteristic

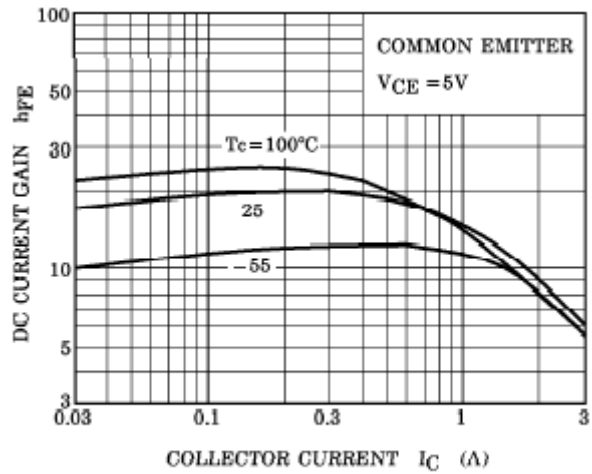


Fig.4 DC current Gain

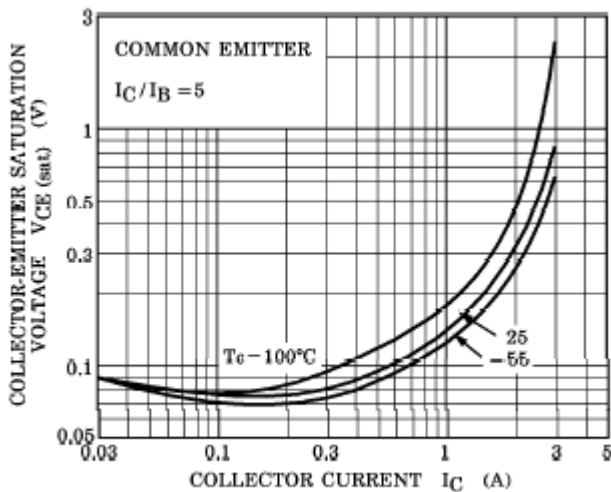


Fig.5 Collector-Emitter Saturation Voltage

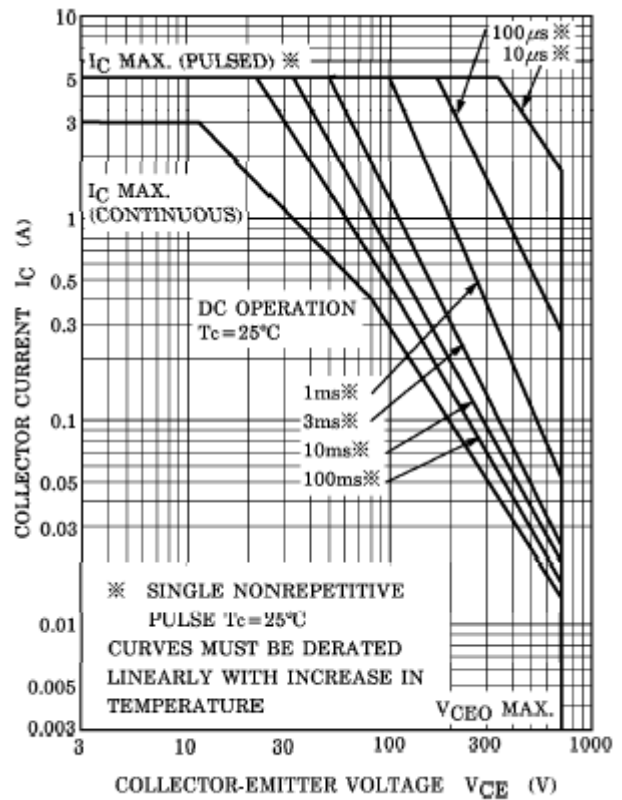


Fig.7 Safe Operating Area

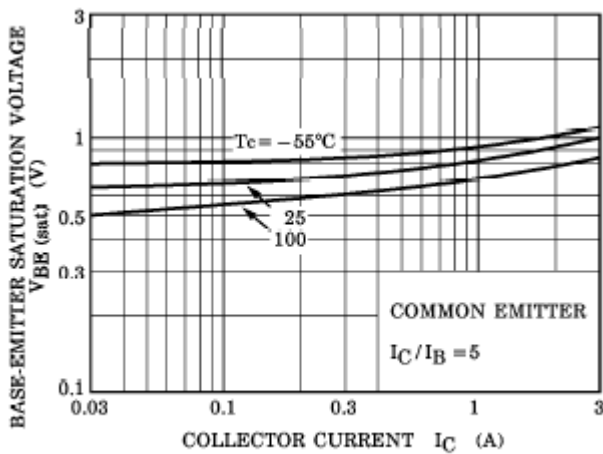


Fig.6 Base-Emitter Saturation Voltage